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ABSTRACT

0039        A method for protecting a semiconductor process wafer surface from contacting thermally degraded photoresist including providing a semiconductor process wafer having a process surface; forming a protective layer over selected areas of the process surface said protective layer including a resinous organic material having a glass transition temperature ( $T_g$ ) that is about greater than a thermal treatment temperature; forming a photoresist layer over at least a portion of the protective layer to include a photolithographic patterning process; and subjecting the semiconductor process wafer to the thermal treatment temperature.